	80A
	30V
	5.3mq

- Advanced Trench Technology
- Excellent RDS(ON) and Low Gate Charge

- Load Switch
- PWM Application
- Power Management

Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	30	-	-
Zero Gate Voltage Drain Current	V_{DS} =30 V, V_{GS} = 0 V	-	-	1
Gate Body Leakage Current	V_{GS}=Ñ20V, V_{DS}=0V	-	-	±100
Gate Threshold Voltage	V_{DS}= V_{GS}, I_D=250εA	1	-	2
Drain-Source on-Resistance	V_{GS}=10V, I_D=30A	-	3.9	5.3
	V_{GS} = 4.5 V, I_D = 25 A			

Figure 1: Output Characteristics

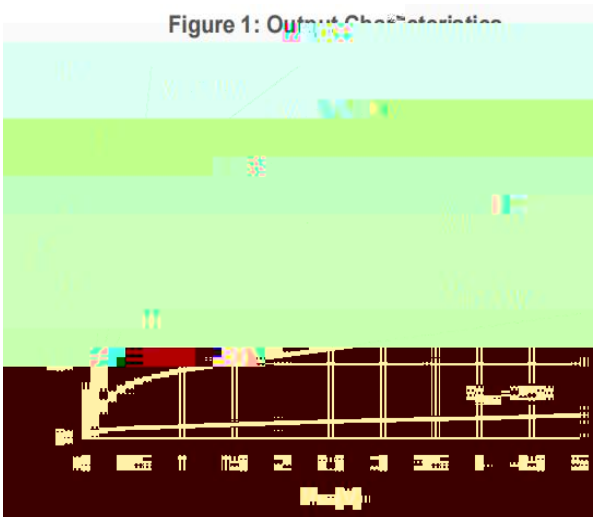


Figure 2: Typical Transfer Characteristics

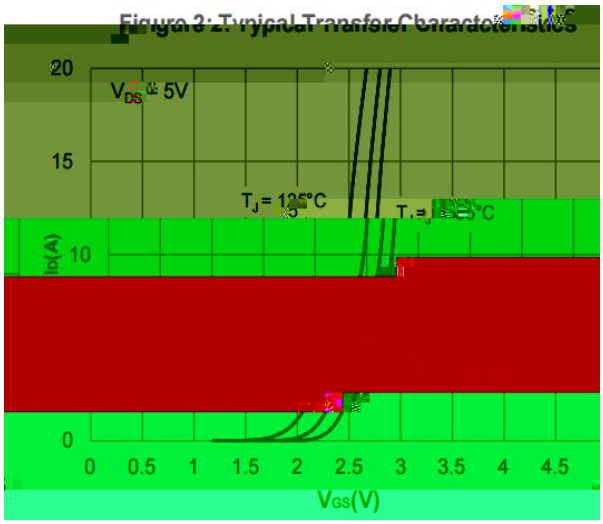


Figure 3: On-resistance vs. Drain Current

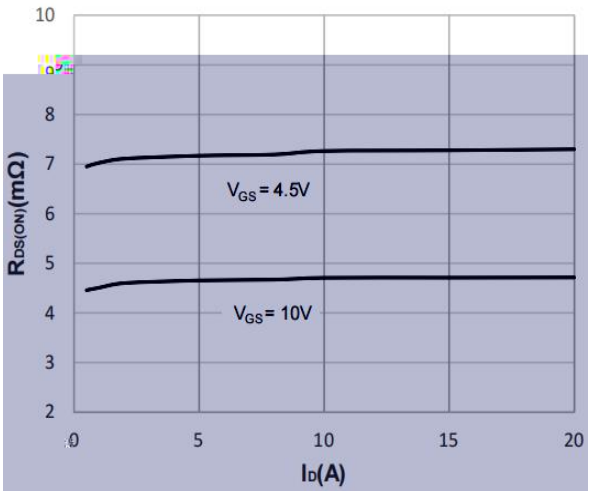


Figure 4: Body Diode Characteristics

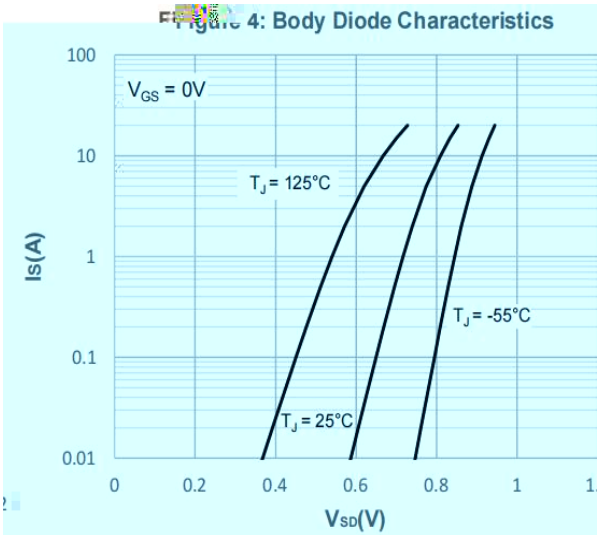


Figure 5: Gate Charge Characteristics

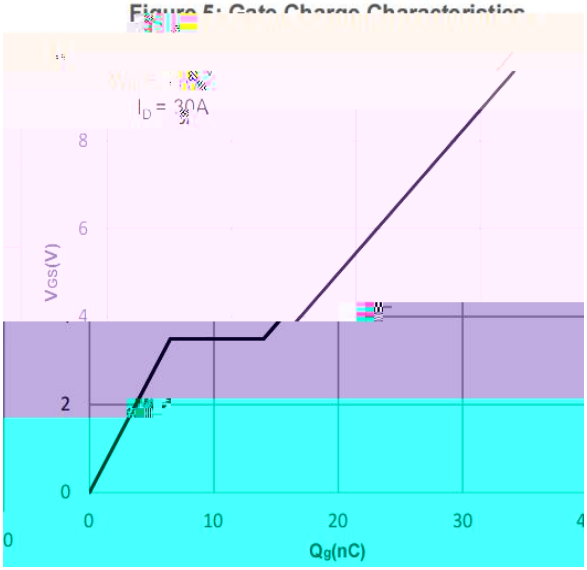


Figure 6: Capacitance Characteristics



YFW80N03NF					

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